

Abstract of the Disclosure:

A semiconductor memory has a novel geometry of a memory cell array. Without reducing the distance between storage capacitors that are the most closely adjacent to one another  
5 it is possible to structure additional lines between adjacent lines in particular word lines. In a preferred embodiment, the number of word lines required for the number of memory cells remaining the same is reduced, as a result of which word line drivers are saved and substrate area is gained.

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